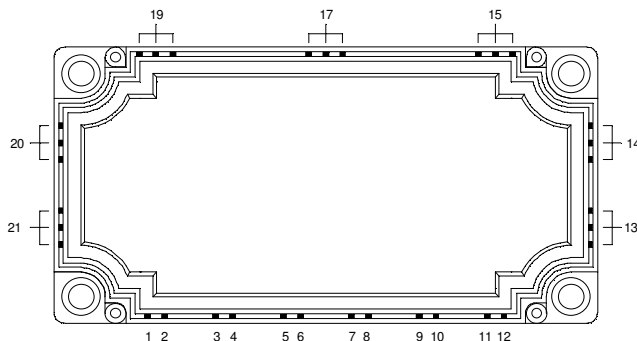
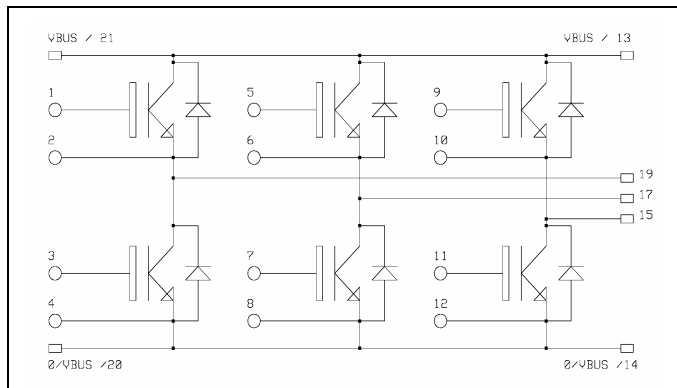


3 Phase bridge NPT IGBT Power Module

**$V_{CES} = 1200V$
 $I_C = 50A @ T_c = 80^\circ C$**



Application

- AC Motor control

Features

- Non Punch Through (NPT) IGBT®
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	78
		$T_C = 80^\circ C$	50
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	150
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	400
SCSOA	Short Circuit Safe Operating Area	$T_j = 125^\circ C$	500A@1200V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 3mA$	1200			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ $V_{CE} = 1200V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	0.8 4	1	mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_C = 50A$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	2.0 3.1	2.5 3.7	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2mA$	4.5		6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		3300		pF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		500		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		220		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		44		ns
T_r	Rise Time	$V_{GE} = \pm 15V$		56		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$		380		
T_f	Fall Time	$I_C = 50A$ $R_G = 22\Omega$		70		

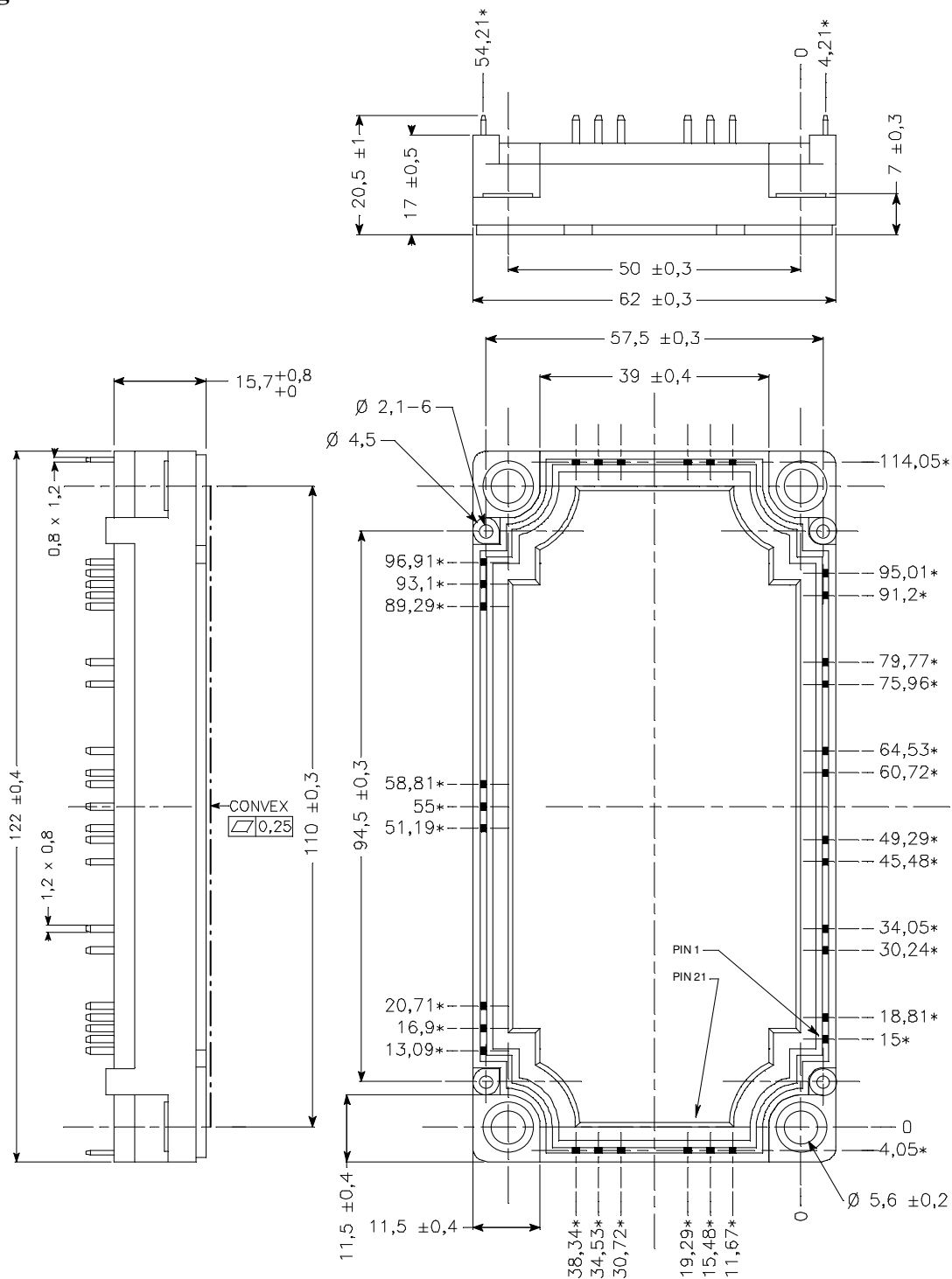
Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode Forward Voltage	$I_F = 50A$ $V_{GE} = 0V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	2.3 1.8	2.8	V
t_{rr}	Reverse Recovery Time	$I_F = 50A$ $V_R = 600V$ $di/dt = 800A/\mu s$	$T_j = 125^\circ\text{C}$	200		ns
Q_{rr}	Reverse Recovery Charge	$I_F = 50A$ $V_R = 600V$ $di/dt = 800A/\mu s$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	2.8 8		μC

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case			IGBT		0.35	°C/W
				Diode		0.7	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		125	
Torque	Mounting torque	To Heatsink	M5	3		4.5	N.m
Wt	Package Weight					300	g

Package outline



ALL DIMENSIONS MARKED " * " ARE TOLERANCED AS : $\pm 0,4$

APT reserves the right to change, without notice, the specifications and information contained herein

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